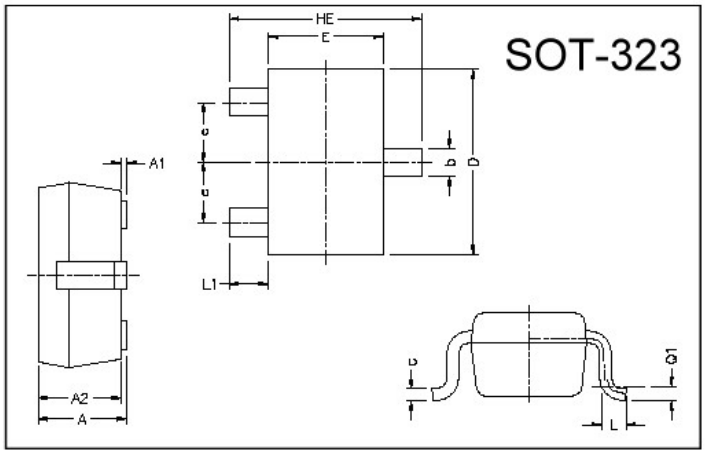
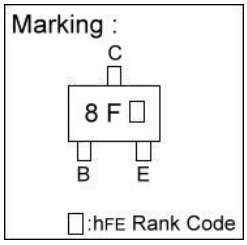
GSBC817 NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GSBC817 is designed for switching and AF amplifier application, suitable for driver storages and low power output storages.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	VCBO	50	V
Collector to Emitter Voltage	VCEO	45	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	800	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25℃

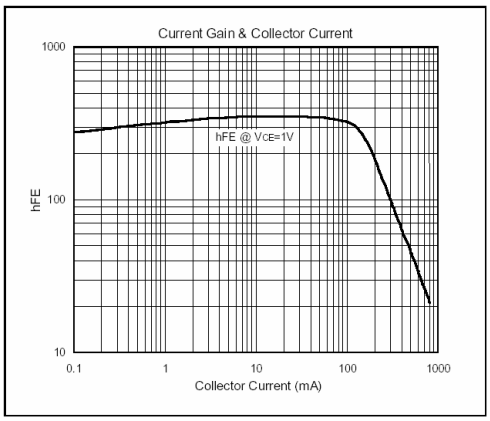
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	50	-	-	V	IC=100uA
BVCEO	45	-	-	V	IC=10mA
BVCES	50	-	-	V	IC=100uA
BVEBO	5	-	-	V	IE=100uA
ICES	-	-	100	nA	VCE=25V
IEBO	-	-	100	nA	VEB=4V
*VCE(sat)	-	-	700	mV	IC=500mA, IB=50mA
*VBE(on)	-	-	1.2	V	VCE=1V, IC=300mA
*hFE	100	-	630		VCE=1V, IC=100mA
fT	-	100	-	MHz	VCE=5V, IC=10mA, f=100MHz
Cob	-	-	12	pF	VCB=10V, f=1MHz, IE=0A

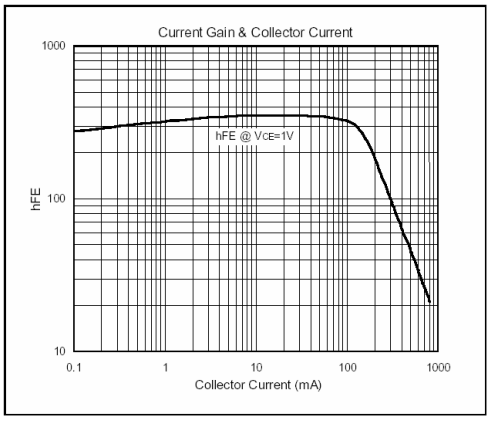
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

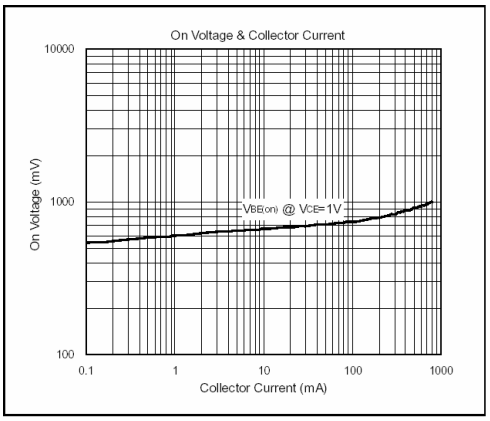
Classification Of hFE

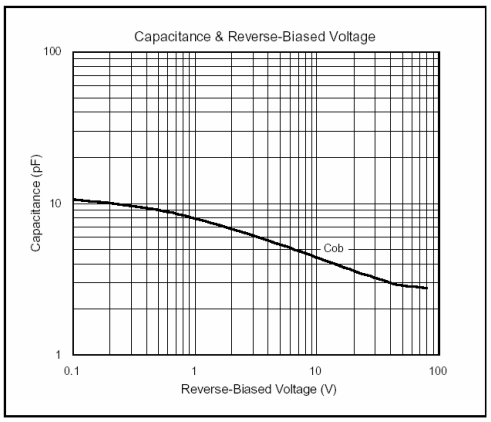
Rank	8FA	8FB	8FC
Range	100 - 250	160 - 400	250 - 630

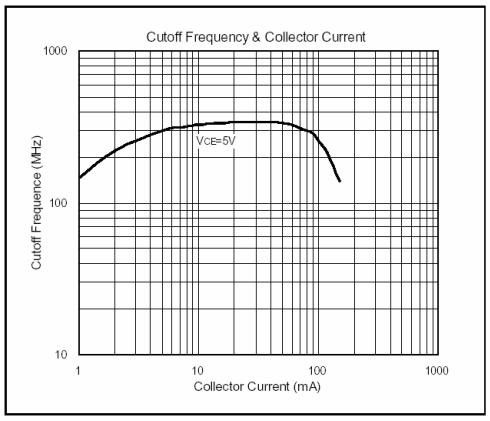
Characteristics Curve











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